

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

ATTY DOCKET NO.
SETI-0002

SERIAL NO. 10/647,714
~~00/986,339~~

Khan et al.

FILING
09/27/2001

GROUP
2818

U.S. PATENT DOCUMENTS

| *EXAMINER INITIAL | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE IF APPROPRIATE |
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FOREIGN PATENT DOCUMENTS

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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| TL | | "Optoelectronic GaN-based Field Effect Transistors," M. S. Shur et al., SPIE, Vol. 2397, pp. 294-303, Feb. 7, 1995. |
| TL | | "High Pinch-off Voltage AlGaIn-GaN Heterostructure Field Effect Transistor," M. S. Shur et al., Proceedings of ISDRS-97, pp. 377-380, Charlottesville, VA, Dec. 1997. |

EXAMINER

Shur

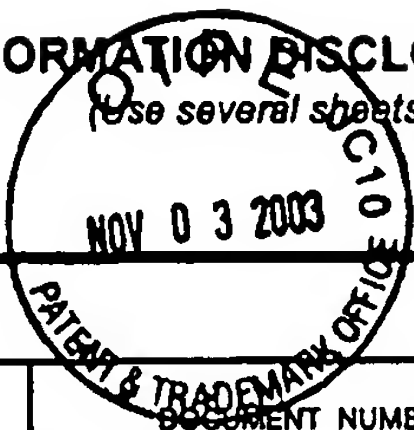
DATE CONSIDERED

2/8/04

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INFORMATION DISCLOSURE CITATION

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| TL | | "DC, Microwave, and High-Temperature Characteristics of GaN FET Structures," S. C. Binari et al., Inst. Phys. Conf. Ser. No. 141: Chapter 4, Presented at Int. Symp. Compound Semicond., San Diego, CA, Sept. 18-22, 1994, pp. 459-462. |
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EXAMINER

Thick

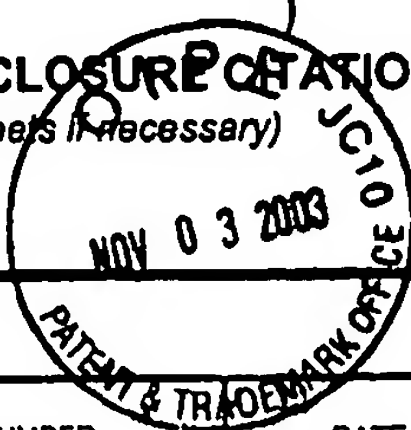
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INFORMATION DISCLOSURE STATEMENT

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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| <div data-bbox="141 2113 262 2184"> </div> | <div data-bbox="414 2059 1932 2104"> <p>"Low Dark Current Transparent Schottky Barrier UV Detectors," G. Simin et al., ICNS3, Montpellier, June 1999.</p> </div> |
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INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

SETI-006

Application Number

09/966559

Applicant(s)

Khan et al.

Filing Date

9/27/2001

Group Art Unit

2818

*EXAMINER

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Applicant(s): Khan et al.

FILING

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U.S. PATENT DOCUMENTS

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